Mehmet Ã¶ztÃ¼rk

List of Publications by Year
in descending order

42 papers	1,274 citations	759055 12 h-index	395590 33 g-index
42 all docs	42 docs citations	42 times ranked	1604 citing authors

#	Article	IF	Citations
1	Designing thermoelectric generators for self-powered wearable electronics. Energy and Environmental Science, 2016, 9, 2099-2113.	15.6	299
2	Flexible thermoelectric generator using bulk legs and liquid metal interconnects for wearable electronics. Applied Energy, 2017, 202, 736-745.	5.1	260
3	Flexible Technologies for Self-Powered Wearable Health and Environmental Sensing. Proceedings of the IEEE, 2015, 103, 665-681.	16.4	166
4	Flexible thermoelectric generators for body heat harvesting â€“ Enhanced device performance using high thermal conductivity elastomer encapsulation on liquid metal interconnects. Applied Energy, 2020, 262, 114370.	5.1	113
5	Energy Harvesting and Storage with Soft and Stretchable Materials. Advanced Materials, 2021, 33, e2004832.	11.1	91
6	Selective lowâ€pressure chemical vapor deposition of Si1â^'xGexalloys in a rapid thermal processor using dichlorosilane and germane. Applied Physics Letters, 1990, 57, 2092-2094.	1.5	53
7	Flexible thermoelectric generator with liquid metal interconnects and low thermal conductivity silicone filler. Npj Flexible Electronics, 2021, 5, .	5.1	44
8	High Thermal Conductivity Silicone Elastomer Doped with Graphene Nanoplatelets and Eutectic GaIn Liquid Metal Alloy. ECS Journal of Solid State Science and Technology, 2019, 8, P357-P362.	0.9	37
9	Growth Kinetics, Silicon Nucleation on Silicon Dioxide, and Selective Epitaxy Using Disilane and Hydrogen in an Ultrahigh Vacuum Rapid Thermal Chemical Vapor Deposition Reactor. Journal of the Electrochemical Society, 1994, 141, 3269-3273.	1.3	35
10	Tuning of the Platinum Silicide Schottky Barrier Height on n-Type Silicon by Sulfur Segregation. IEEE Electron Device Letters, 2009, 30, 331-333.	2.2	31
11	Tuning of the Nickel Silicide Schottky Barrier Height on p-Type Silicon by Indium Implantation. IEEE Electron Device Letters, 2009, 30, 1272-1274.	2.2	23
12	Low temperature silicon epitaxy in an ultrahigh vacuum rapid thermal chemical vapor deposition reactor using disilane. Applied Physics Letters, 1993, 63, 1225-1227.	1.5	16
13	Low-Pressure Chemical Vapor Deposition of Polycrystalline Silicon and Silicon Dioxide By Rapid Thermal Processing. Materials Research Society Symposia Proceedings, 1989, 146, 109.	0.1	14
14	Characterization of LPCVD of Silicon Nitride in a Rapid Thermal Processor. Materials Research Society Symposia Proceedings, 1989, 146, 345.	0.1	13
15	Influence of dry and wet cleaning on the properties of rapid thermal grown and deposited gate dielectrics. Journal of Electronic Materials, 1993, 22, 335-339.	1.0	13
16	Silicon Nucleation and Film Evolution on Silicon Dioxide Using Disilane: Rapid Thermal Chemical Vapor Deposition of Very Smooth Silicon at High Deposition Rates. Journal of the Electrochemical Society, 1996, 143, 649-657.	1.3	9
17	Source/Drain Junctions and Contacts for 45 nm CMOS and Beyond. AIP Conference Proceedings, 2005, , .	0.3	8
18	Platinum Germanosilicide Contacts Formed on Strained and Relaxed $hbox{Si}_{1 - x}hbox{Ge}_{x}$ Layers. IEEE Transactions on Electron Devices, 2009, 56, 1220-1227.	1.6	8

#	Article	IF	Citations
19	Low pressure chemical vapor deposition of silicon dioxide below 500â€‰Â°C by the pyrolysis of diethylsilane in oxygen. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1992, 10, 625.	1.6	7
20	Impact of Ge on integration of HfO2 and metal gate electrodes on strained Si channels. Applied Physics Letters, 2005, 87, 071903.	1.5	7
21	Schottky Barrier Height of Erbium Silicide on $ hbox{Si}_{1 - x}hbox{C}_{x}$. IEEE Electron Device Letters, 2009, 30, 949-951.	2.2	6
22	Low Thermal Budget In Situ Surface Cleaning for Selective Silicon Epitaxy. Journal of the Electrochemical Society, 1998, 145, 3602-3609.	1.3	5
23	Characterization of Oxygen-Doped and Non-Oxygen-Doped Polysilicon Films Prepared by Rapid Thermal Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 1993, 303, 49.	0.1	2
24	Self-Aligned Formation of C54 Titanium Germanosilicide Using Rapid Thermal Processing and Application to Raised, Ultrashallow Junctions. Materials Research Society Symposia Proceedings, 1993, 320, 311.	0.1	2
25	Formation of Raised Source/Drain Junctions by Rapid Thermal Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 1995, 387, 355.	0.1	2
26	Nickel, Platinum and Zirconium Germanosilicide Contacts to Heavily Phosphorous Doped Silicon-Germanium Alloys for Advanced CMOS Source/Drain Junctions. Materials Research Society Symposia Proceedings, 2002, 745, 4111.	0.1	2
27	Schottky Barrier Height of Nickel Silicide Contacts Formed on $hbox{Si}_{1 - x}hbox{C}_{x}$ Epitaxial Layers. IEEE Electron Device Letters, 2009, 30, 1320-1322.	2.2	2
28	High Quality Silicon Epitaxy In An Ultra High Vacuum Rapid Thermal Cvd Reactor: An Application to Single Wafer Processing. Materials Research Society Symposia Proceedings, 1993, 303, 25.	0.1	1
29	A Novel Implantation Free Raised Source/Drain Mosfet Process Using Selective Rapid Thermal Chemical Vapor Deposition Of In-Situ Boron Doped Si_xGe_{1-x}. Materials Research Society Symposia Proceedings, 1993, 303, 37.	0.1	1
30	Silicon Etching in Rapid Thermal Chemical Vapor Deposition of Tisi2. Materials Research Society Symposia Proceedings, 1995, 387, 443.	0.1	1
31	IS Selective CVD an Improvement for the Titanium Silicide Process in Sub-Quarter Micron Technology? A Phase Formation Study Using X-ray Diffraction. Materials Research Society Symposia Proceedings, 1998, 514, 243.	0.1	1
32	Is Selective Cvd an Improvement for the Titanium Silicide Process in Sub-Quarter Micron Technology? A Phase Formation Study Using X-Ray Diffraction. Materials Research Society Symposia Proceedings, 1998, 514, 439.	0.1	1
33	Energy Harvesting and Storage: Energy Harvesting and Storage with Soft and Stretchable Materials (Adv. Mater. 19/2021). Advanced Materials, 2021, 33, 2170151.	11.1	1
34	Application of Constant Absorptivity Ring (Car) to Improve Polysilicon Thickness Uniformity In A Rapid Thermal Chemical Vapor Deposition Reactor. Materials Research Society Symposia Proceedings, 1993, 303, 19.	0.1	0
35	Cleaning during Initial Stages of Epitaxial Growth in an Ultrahigh Vacuum Rapid Thermal Chemical Vapor Deposition Reactor. Materials Research Society Symposia Proceedings, 1993, 334, 463.	0.1	0
36	Silicon Nucleation on Silicon Dioxide and Selective Epitaxy In An Ultra-High Vacuum Raptid Thermal Chemical Vapor Deposition Reactor Using Disilane In Hydrogen. Materials Research Society Symposia Proceedings, 1993, 334, 519.	0.1	0

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37	Characterization of MOS Devices Fabricated on Carbon Implanted Silicon Substrates. Materials Research Society Symposia Proceedings, 1995, 378, 737.	0.1	0
38	Low Temperature Selective Silicon Epitaxy Using Si2H6, H2 and Cl2 in Ultra High Vacuum Rapid Thermal Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 1995, 387, 335.	0.1	0
39	Formation of Ultra-Shallow Junctions in Silicon by Rapid Thermal Vapor Phase Doping in an Ultrahigh Vacuum Rapid Thermal Processing System. Materials Research Society Symposia Proceedings, 1995, 387, 395.	0.1	0
40	Selective Rapid Thermal Chemical Vapor Deposition of Titanium Disilicide on Silicon and Polysilicon. Materials Research Society Symposia Proceedings, 1997, 470, 139.	0.1	0
41	Low Resistivity Nickel Germanosilicide Contacts to Ultra-shallow Junctions Formed by the Selective Si1-xGexTechnology for Nanoscale CMOS. Materials Research Society Symposia Proceedings, 2003, 765, 1.	0.1	0
42	Impact of Heavy Boron Doping and Nickel Germanosilicide Contacts on Biaxial Compressive Strain in Pseudomorphic Silicon-Germanium Alloys on Silicon. Materials Research Society Symposia Proceedings, 2006, 913, 1.	0.1	0